

In the Specification:

Please insert before the first paragraph of the application:

This application is the national stage application of international application number PCT/DE2003/02523, filed on July 26, 2003, which claims the benefit of priority to German Patent Application DE 10234694.1, filed on July 30, 2002, incorporated herein by reference.

Please rewrite the paragraph on page 2, lines 13-22 as follows:

~~The object relating to the method is achieved by the method steps described in patent claim 1.~~ In addition to the method steps described in the introduction, in the method according to the invention the substrate is preferably processed in a single-substrate process in the heating device. Moreover, during the processing the process temperature is recorded via the temperature at a holding device for the substrate. The holding device mainly contains a material with a high thermal conductivity at the process temperature.

Please rewrite the paragraph on page 17, lines 4-11 as follows:

In a heat-up phase between a time t_0 and a time t_1 at approximately 130 seconds, the graphite box 110 and therefore also the semiconductor substrate ~~42-14~~ is then heated to a temperature of 400°C. On account of the temperature being recorded at the base surface 112 and of suitable control constants being selected, the temperature curve 160 does not significantly overshoot the temperature value 400°C.